

DHG10I600PM

preliminary

 $V_{RRM} = 600 V$

 $I_{FAV} = 10 A$

 $t_{rr} = 35 \, \text{ns}$

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Sonic Fast Recovery Diode

Part number

DHG10I600PM



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

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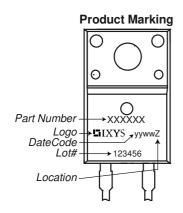
Fast Diode					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			600	V
IR	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			30	μΑ
		$V_R = 600 \text{ V}$	$T_{VJ} = 125^{\circ}C$			1.2	mΑ
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			2.23	V
		$I_F = 20 A$				3.13	٧
		I _F = 10 A	T _{VJ} = 125°C			2.18	V
		$I_F = 20 \text{ A}$				3.29	٧
I FAV	average forward current	$T_C = 25^{\circ}C$	T _{vJ} = 150°C			10	Α
		rectangular d = 0.5					1 1 1 1
V _{F0}	threshold voltage		T _{VJ} = 150°C			1.04	V
\mathbf{r}_{F}	slope resistance	ss calculation only				104	mΩ
R _{thJC}	thermal resistance junction to case	;				4	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.5		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			30	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			80	Α
CJ	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		6		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		4		Α
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}$	$T_{VJ} = {}^{\circ}C$		tbd		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 10 \text{ A}; V_R = 200 \text{ V} \\ -di_F /dt = 200 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		35		ns
	J		$T_{VJ} = {}^{\circ}C$		tbd		ns



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Package TO-220FP			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					35	Α
T _{VJ}	virtual junction temperature				-55		150	°C
Top	operation temperature				-55		125	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	N
$d_{\text{Spp/App}}$	creepage distance on surface	etriking dietance through air	terminal to terminal	3.2	2.7			mm
$d_{Spb/Apb}$	creepage distance on surface [striking distance through an	terminal to backside	2.5	2.5			mm
V _{ISOL}	isolation voltage	plation voltage t = 1 second			2500			٧
		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		2100			٧



Part description

D = Diode H = Sonic Fast Recovery Diode

G = extreme fast

10 = Current Rating [A]

I = Single Diode

600 = Reverse Voltage [V] PM = TO-220ACFP (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10l600PM	DHG10l600PM	Tube	50	503679

Similar Part	Package	Voltage class	
DHG10I600PA	TO-220AC (2)	600	

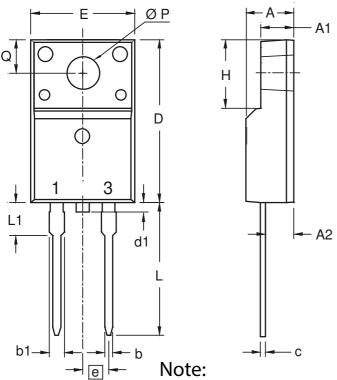
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150$ °C
$I \rightarrow V_0$	— R ₀ —	Fast Diode		
V _{0 max}	threshold voltage	1.04		V
$R_{0 max}$	slope resistance *	101		$m\Omega$





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Outlines TO-220FP



Note:
All metal surface are
matte pure tin plated
except trimmed area.

Dim.	Millimeters		Inches		
ווווט.	min	max	min	max	
Α	4.50	4.90	0.177	0.193	
A1	2.34	2.74	0.092	0.108	
A2	2.56	2.96	0.101	0.117	
b	0.70	0.90	0.028	0.035	
b1	1.27	1.47	0.050	0.058	
С	0.45	0.60	0.018	0.024	
D	15.67	16.07	0.617	0.633	
d1	0	1.10	0	0.043	
Е	9.96	10.36	0.392	0.408	
е	2.54	BSC	0.100	BSC	
Н	6.48	6.88	0.255	0.271	
L	12.68	13.28	0.499	0.523	
L1	3.03	3.43	0.119	0.135	
ØΡ	3.08	3.28	0.121	0.129	
Q	3.20	3.40	0.126	0.134	



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